

**PCN #171**  
**Notification Date:**  
**22 April 2019**

## Product / Process Change Notice

**Parts Affected:**

Chip process CP391, N-Channel MOSFETs, wafers and bare die

**Extent of Change:**

The CP391 wafer process has been discontinued and replaced with the CP399 wafer process. See figures 1 and 2 for details.

**Reason for Change:**

The CP391 wafer process has been replaced to the CP399 wafer process in order to enhance the manufacturing process controls and performance. The wafer size has increased from 6 inch to 8 inch in order to improve throughput. In addition, this change is being made to ensure uninterrupted supply of product, moving forward.

**Effect of Change:**

The wafer process meets all electrical specifications of the individual devices listed on the following page.

**Qualification:**

P/N: CP399 Chip Process

Package: TO-220FP

No.	Test	Conditions (Reference standards are in bold)	Qty	Pass/Fail	Test Results
<b>1</b>	<b>Device Life Tests</b>				
a	High Temperature Gate Reverse Bias (HTGB)	T=150°C, t = 1000 hours 100% VGS=30V <b>JESD22-A110</b>	45	Pass	45/45
b	High Temperature Reverse Bias (HTRB)	T=150°C, t = 1000 hours VDS=600V <b>JESD22-A108</b>	45	Pass	45/45
c	High Accelerated Temperature and Humidity Stress Test (HAST)	T=130°C, t = 96 hours, 85%RH, 230kPA, VDS=42V <b>JESD22-A108</b>	45	Pass	45/45
D	Temperature Cycling (TC)	-65°C -+150°C, Tdwell ≥10min, 500 cycles	45	Pass	45/45

**Effective Date of Change:**

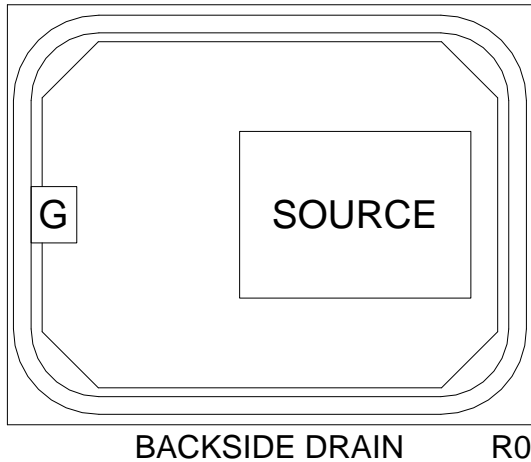
Existing inventory of chip process CP391 will be shipped until depleted.

**PCN #171**  
**Notification Date:**  
**22 April 2019**

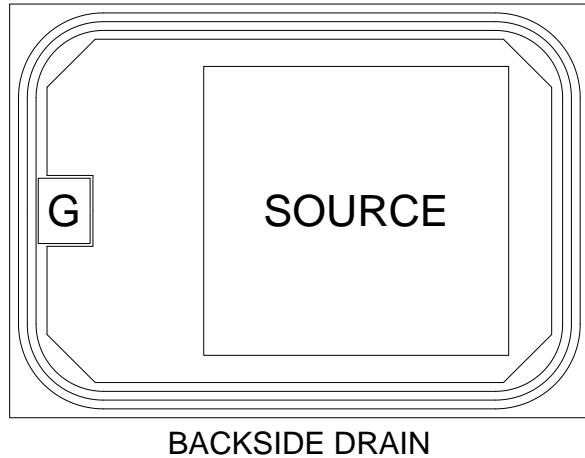
**Sample Availability:**

Please contact your salesperson or manufacturer's representative for samples.

**Figure 1: CP391 Chip Geometry (Discontinued)**



**Figure 2: CP399 Chip Geometry**



Wafer Diameter: 6 inch  
Die Size: 161 x 129 mils  
Die Thickness: 9.1 mils  
Bond Pad Size (Gate): 14 x 17.3 mils  
Bond Pad Size (Source): 70.9 x 51.2 mils  
Topside Metal: Al (43,000Å)  
Backside Metal: Ag (8000Å)

Wafer Diameter: 8 inch  
Die Size: 149.6 x 107.1 mils  
Die Thickness: 9.1 mils  
Bond Pad Size (Gate): 13.4 x 16.9 mils  
Bond Pad Size (Source): 78.7 x 74.8 mils  
Topside Metal: Al (43,000Å)  
Backside Metal: Ag (8000Å)

**Part Numbers Affected:**

CDM22011-600LRFP	CP391-CDM11-600L-WN
	CP391-CDM11-600L-CT



145 Adams Avenue, Hauppauge, NY 11788 USA  
Tel: (631) 435-1110 • Fax: (631) 435-1824  
[www.centalsemi.com](http://www.centalsemi.com)  
<mailto:processchange@centalsemi.com>  
<http://www.centalsemi.com/processchange>

**PCN #171**  
**Notification Date:**  
**22 April 2019**

As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	